

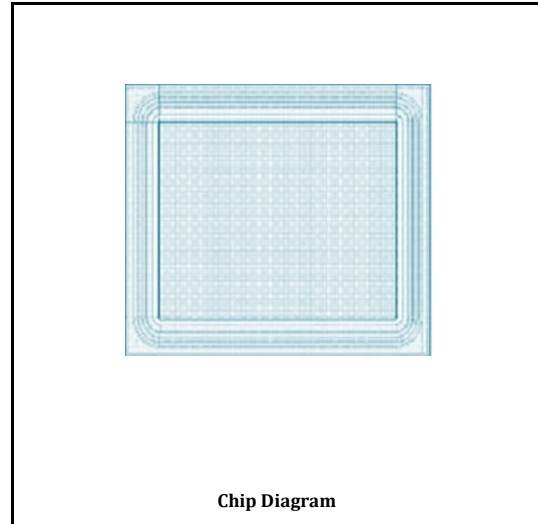
PRODUCT FEATURES

- ◆ Ultrafast Recovery Time
- ◆ Soft Recovery Characteristics
- ◆ Low Forward Voltage
- ◆ Low Leakage Current
- ◆ Planar structure

Applications (not limited to)

- ◆ Freewheeling, Snubber, Clamp
- ◆ Snubber Diode
- ◆ Switch Power Supplies
- ◆ Motor control
- ◆ Inverters, Converters

Items	Description
Wafer Size	5 Inch
Gross Die	2700 EA
Top Metal	Al
Back Metal	Ag
Dimensions	um
Chip Size	2000um * 2000um
Pad Size	1210um * 1210um
Wafer Thickness	260±20um
Scribe Line width (E)	60 um
Bonding Wire	Al, 15mil*1



Absolute Maximum ratings (T_a=25℃)

Parameter	Symbol	Value	Units
DC Blocking Voltage	V _{RRM}	800	V
Average Rectified Forward Current	I _{FAV}	8	A
Nonrepetitive Peak Surge Current@8.3mS	I _{FSM}	80	A
Operating Junction Temperature	T _j	175	℃
Storage Temperature	T _{STG}	- 55~150	℃

Electrical specification (T_a=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Breakdown Voltage	V _{BR}	I _R =50μA	800	880	-	V
Forward Voltage	V _F	I _F =8A, T _a =25℃	-	1.70	2.00	V
		I _F =8A, T _a =125℃	-	1.55	1.85	V
Reverse Leakage Current	I _R	V _R =800V, T _a =25℃	-	-	2	μA
		V _R =800V, T _a =125℃	-	-	50	μA
Reverse Recovery Time	T _{rr}	I _F =0.5A, I _R =1A, I _{rr} =0.25A	-	30	45	ns
		I _F =1A, V _R =30V, di/dt=-200A/us	-	28	-	ns

Remark:

- 1.Customer should obtain the latest version of datasheet before placing order, and verify the relevant information.
- 2.Cutting damage and chipping area can't beyond scribe line in given size range.
- 3.Testing system of T_{rr} could be different, customer might take secondary test to evaluate if necessary.
- 4.Customer might choose the bonding wire material and diameter according to actual situation, while no less than our recommendation.